imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

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Features and Benefits

- PWM and quasi-resonant topology
- Integrated on-time control circuit (it realizes high power factor by average current control)
- Integrated soft-start circuit (reduces power stress during start-up on the incorporated power MOSFET and output rectifier)
- Integrated bias assist circuit (improves startup performance, suppresses V_{CC} voltage droop during operation, and allows use of low-rated ceramic capacitor on VCC pin)
- Integrated Leading Edge Blanking (LEB) circuit
- Integrated maximum on-time limit circuit
- Protection features:
- ^o Overcurrent protection (OCP): pulse-by-pulse
- Overvoltage protection (OVP): latched shutdown
- Overload protection (OLP): latched shutdown
- Thermal shutdown (TSD): latched shutdown

Package: 8-pin DIP



Not to scale

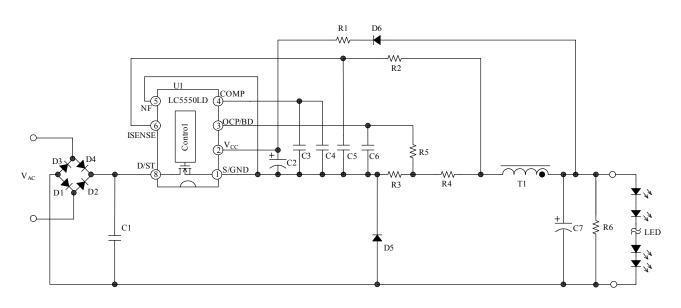
Description

LC5550LD series are PWM and quasi-resonant topology non-isolated buck LED driver ICs. They incorporate separate controller and power MOSFET chips, and are designed for input capacitorless applications. The controller adapts the average current control method for realizing high power factors. The rich set of protection features helps to realize low component counts, and high performance-to-cost power supply.

Applications

- LED lighting fixtures
- LED light bulbs

Typical Application



Selection Guide

Part Number	MOSFET V _{DSS} (min) (V)	R _{DS(on)} (max) (Ω)	PWM Operation Frequency, f _{OSC} (typ) (kHz)	On-Time t _{ON(MAX)} (typ) (µs)
LC5555LD	650	3.95	72	9.3
LC5556LD	650	1.9	60	11.2

*Based on the thermal rating; the allowable maximum output power can be up to 120% to 140% of this value. However, maximum output power may be limited in such an application with low output voltage or short duty cycle.

The polarity value for current specifies a sink as "+," and a source as "-," referencing the IC.

LC5550LD Absolute Maximum Ratings Unless specifically noted, T_A is 25°C

Characteristic	Symbol		Notes	Pins	Rating	Unit
Drain Current ¹		LC5555LD	Single pulse	8 – 1	2.5	A
Diam Current	DPeak	LC5556LD	Single pulse	8 – 1	4.0	A
Single Pulse Avalanche Energy ²	E _{AS}	LC5555LD	I_{LPeak} = 2.0A, V_{DD} = 99 V, L = 20 mH	8 – 1	47	mJ
Single Pulse Avalanche Energy ²		LC5556LD	I _{LPeak} = 2.7A, V _{DD} = 99 V, L = 20 mH	8 – 1	86	mJ
Input Voltage for Control Part (MIC)	V _{CC}			2 – 1	35	V
OCP/BD Pin Voltage	V _{OCP}			3 – 1	-2.0 to 5.0	V
COMP Pin Voltage	V _{COMP}			4 – 1	-0.3 to 7.0	V
ISENSE Pin Voltage	V _{SEN}			6 – 1	-0.3 to 5.0	V
Allowable Power Dissipation of MOSFET ³	P _{D1}	Mounted on	a 15 mm × 15 mm PCB	8 – 1	0.97	W
Operating Ambient Temperature	T _{OP}			—	-55 to 125	°C
Storage Temperature	T _{stg}			_	-55 to 125	°C
Channel Temperature	T _{ch}			_	150	°C

¹Refer to MOSFET Safe Operating Area Curve.

²Refer to MOSFET Avalanche Energy Derating Coefficient Curve.

³Refer to MOSFET Temperature versus Power Dissipation Curve.

LC5550LD Electrical Characteristics of Control Part (MIC) Unless specifically noted, T_A is 25°C, V_{CC} is 18 V

Characteristic	Symbol	Test Conditions	Pins	Min.	Тур.	Max.	Unit
Power Supply Startup Operation							
Operation Start Voltage	V _{CC(ON)}		2 – 1	13.8	15.1	17.3	V
Operation Stop Voltage*	V _{CC(OFF)}		2 – 1	8.4	9.4	10.7	V
Circuit Current in Operation	I _{CC(ON)}		2 – 1	-	-	4.7	mA
Startup Circuit Operation Voltage	VSTARTUP		8 – 1	18	21	24	V
Startup Current	I _{CC(STARTUP)}	V _{CC} = 13 V	2 – 1	-8.5	-4.0	-1.5	mA
Startup Current Threshold Biasing Voltage*	V _{CC(BIAS)}		2 – 1	9.5	11.0	12.5	V
Normal Operation			·				
	£	LC5555LD	0 1	60	72	84	kHz
PWM Operation Frequency	f _{osc}	LC5556LD	8 – 1	50	60	70	kHz
Maximum On Time	t _{on(MAX)}	LC5555LD	0 1	8.0	9.3	11.2	μs
Maximum On-Time		LC5556LD	8 – 1	9.0	11.2	13.4	μs
COMP Pin Control Minimum Voltage	V _{COMP(MIN)}		4 – 1	0.30	0.55	0.80	V
Error Amplifier Reference Voltage	V _{SEN(TH)}		6 – 1	-0.21	-0.2	-0.19	V
Error Amplifier Source Current	I _{SEN(SOURCE)}		4 – 1	-36	-24	-12	μA
Error Amplifier Sink Current	I _{SEN(SINK)}		4 – 1	12	24	36	μA
Leading Edge Blanking Time	t _{ON(LEB)}		3 – 1	-	600	-	ns
Quasi-Resonant Operation Threshold Voltage-1	V _{BD(TH1)}		3 – 1	0.14	0.24	0.34	V
Quasi-Resonant Operation Threshold Voltage-2	V _{BD(TH2)}		3 – 1	0.11	0.16	0.21	V
Protected Operation			·				
OCP/BD Pin Overcurrent Protection (OCP) Threshold Voltage	V _{OCP}		3 – 1	-0.92	-0.8	-0.68	V
OCP.BD Pin Source Current	I _{OCP}		3 – 1	-120	-40	-10	μA
OCP/BD Pin Overvoltage Protection (OVP) Operation Voltage	V _{BD(OVP)}		3 – 1	2.2	2.6	3.0	V
Overload Protection (OLP) Threshold Voltage	V _{COMP(OLP)}		4 – 1	4.1	4.5	4.9	V
VCC Pin OVP Threshold Voltage	V _{CC(OVP)}		2 – 1	28.5	31.5	34.0	V
Thermal Shutdown Activating Temperature	T _{J(TSD)}		-	135	_	_	°C

 $V_{CC(BIAS)} > V_{CC(OFF)}$ always.

LC5550LD Electrical Characteristics of MOSFET Unless specifically noted, TA is 25°C

Characteristic	Symbol		Test Conditions	Pins	Min.	Тур.	Max.	Unit
Drain-to-Source Breakdown Voltage	V _{DSS}			8 – 1	650	_		V
Drain Leakage Current	I _{DSS}			8 – 1	—	—	300	μA
On-Resistance	R _{DS(ON)}	LC5555LD		8 – 1	—	—	3.95	Ω
On-Resistance		LC5556LD			—	—	1.9	Ω
Switching Time	t _f	LC5555LD		8 – 1	—	—	250	ns
		LC5556LD			—	—	400	ns
Thermal Desistence*	D	LC5555LD			_	—	42	°C/W
Thermal Resistance*	R _{θch-c}	LC5556LD			_	_	35.5	°C/W

*The thermal resistance between the channels of the MOSFET and the case. T_C measured at the center of the case marked side.

Single-Stage Power Factor Corrected High Efficiency Non-Isolated Buck LED Driver

Characteristic Performance LC5555LD MOSFET Safe Operating Area Curve 10 Drain current limited by on-resistance S. O. A. Temperature Derating Coefficient Curve 0.1 ms 100 Safe Operating Area Temperature Derating Coefficient (%) 80 1 ms Drain Current, I_D (A) 1 60 40 0.1 20 0 0 75 125 150 25 50 100 To use this graph, apply the S.O.A Channel Temperature, T_{Ch} (°C) temperature derating coefficient taken from the graph at the left 0.01 10 100 Drain-to-Source Voltage, VDS (V) MOSFET Avalanche Energy Derating Coefficient Curve MOSFET Temperature versus Power Dissipation Curve 100 1.2 P_{D1} (W) Temperature Derating Coefficient (%) 1.0 80 Allowable Power Dissipation, 0.8 60 EAS 0.6 40 0.4 20 0.2 0 ∟ 0 0 └ 25 50 150 25 50 75 100 125 75 100 150 125 Channel Temperature, Tch (°C) Ambient Temperature, TA (°C) Transient Thermal Resistance Curve 10 Transient Thermal Resistance, R_{8ch-c} (°C/W) 1 0.1

0.01 └─ 10^{_6}

10-5

Time (s)

10-3

10-2

10-1

10-4

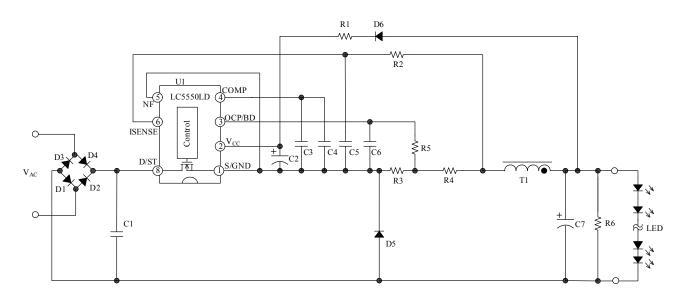
1000

Single-Stage Power Factor Corrected High Efficiency Non-Isolated Buck LED Driver

LC5556LD MOSFET Safe Operating Area Curve 10 0.1 ms S. O. A. Temperature Derating Coefficient Curve 100 Safe Operating Area Temperature Derating Coefficient (%) 80 1 Drain Current, I_D (A) Drain current limited by on-resistance 60 40 0.1 20 0 0 75 125 150 25 50 100 To use this graph, apply the S.O.A Channel Temperature, T_{Ch} (°C) temperature derating coefficient taken from the graph at the left 0.01 10 100 1000 1 Drain-to-Source Voltage, VDS (V) MOSFET Avalanche Energy Derating Coefficient Curve MOSFET Temperature versus Power Dissipation Curve 100 1.2 P_{D1} (W) Temperature Derating Coefficient (%) 1.0 80 Allowable Power Dissipation, 0.8 60 EAS 0.6 40 0.4 20 0.2 0 ∟ 0 0 └ 25 50 150 25 50 75 100 125 75 100 150 125 Channel Temperature, Tch (°C) Ambient Temperature, TA (°C) Transient Thermal Resistance Curve 10 Transient Thermal Resistance, R_{8ch-c} (°C/W) 1 0.1 0.01 🖙 10^{_6} 10-5 10-4 10-3 10-2 10-1

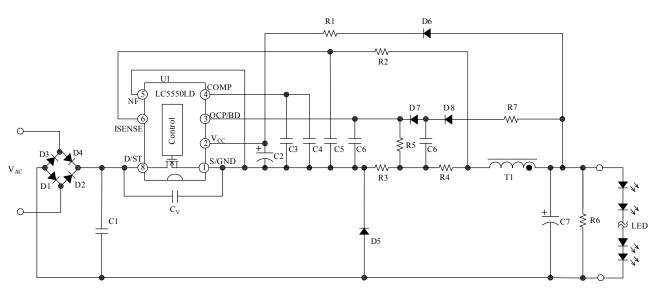
Characteristic Performance

Time (s)

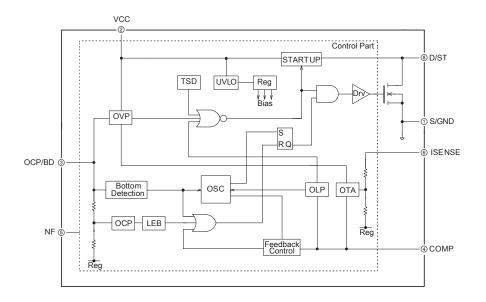


Typical Application Circuit 1, PWM Topology

Typical Application Circuit 2, Quasi-Resonant Topology

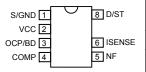


Functional Block Diagram



Pin List Table

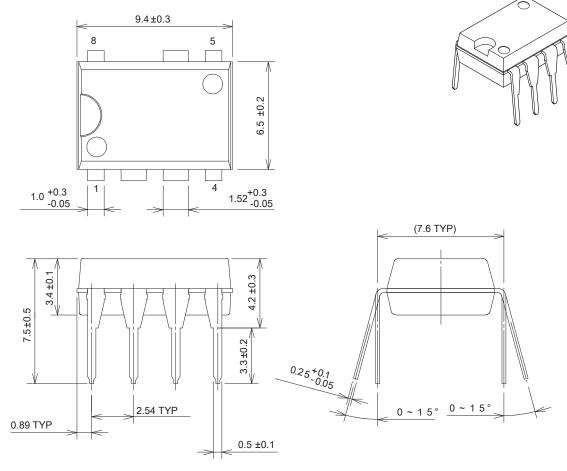
Pin-out Diagram



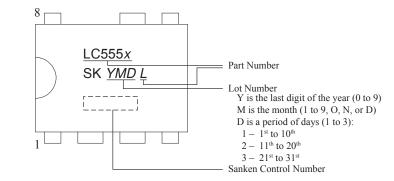
Number	Name	Function
1	S/GND	MOSFET source and GND pin for the Control Part
2	VCC	Supply voltage input and Overvoltage Protection (OVP) signal input
3	OCP/BD	Overcurrent Protection (OCP), quasi-resonant signal input, and Overvoltage Protection (OVP) signal input
4	COMP	Feedback phase-compensation input
5	NF	No function; must be externally connected to S/GND pin with as short a trace as possible, for stable operation of the IC
6	ISENSE	Output current sensing voltage input
7	-	Pin removed
8	D/ST	MOSFET drain pin and input of the startup current

Single-Stage Power Factor Corrected High Efficiency Non-Isolated Buck LED Driver

Package Diagram DIP8 package



Unit: mm





Pb-free. Device composition compliant with the RoHS directive.

Single-Stage Power Factor Corrected High Efficiency Non-Isolated Buck LED Driver

Because reliability can be affected adversely by improper storage environments and handling methods, please observe the following cautions.

Cautions for Storage

- Ensure that storage conditions comply with the standard temperature (5°C to 35°C) and the standard relative humidity (around 40% to 75%); avoid storage locations that experience extreme changes in temperature or humidity.
- Avoid locations where dust or harmful gases are present and avoid direct sunlight.
- Reinspect for rust on leads and solderability of the products that have been stored for a long time.

Cautions for Testing and Handling

When tests are carried out during inspection testing and other standard test periods, protect the products from power surges from the testing device, shorts between the product pins, and wrong connections. Ensure all test parameters are within the ratings specified by Sanken for the products.

Remarks About Using Silicone Grease with a Heatsink

- When silicone grease is used in mounting the products on a heatsink, it shall be applied evenly and thinly. If more silicone grease than required is applied, it may produce excess stress.
- Volatile-type silicone greases may crack after long periods of time, resulting in reduced heat radiation effect. Silicone greases with low consistency (hard grease) may cause cracks in the mold resin when screwing the products to a heatsink.

Our recommended silicone greases for heat radiation purposes, which will not cause any adverse effect on the product life, are indicated below:

Туре	Suppliers
G746	Shin-Etsu Chemical Co., Ltd.
YG6260	Momentive Performance Materials Inc.
SC102	Dow Corning Toray Co., Ltd.

Soldering

- When soldering the products, please be sure to minimize the working time, within the following limits: 260±5°C 10±1 s (Flow, 2 times)
 - 380±10°C 3.5±0.5 s (Soldering iron, 1 time)
- Soldering should be at a distance of at least 1.5 mm from the body of the products.

Electrostatic Discharge

- When handling the products, the operator must be grounded. Grounded wrist straps worn should have at least 1 MΩ of resistance from the operator to ground to prevent shock hazard, and it should be placed near the operator.
- Workbenches where the products are handled should be grounded and be provided with conductive table and floor mats.
- When using measuring equipment such as a curve tracer, the equipment should be grounded.
- When soldering the products, the head of soldering irons or the solder bath must be grounded in order to prevent leak voltages generated by them from being applied to the products.
- The products should always be stored and transported in Sanken shipping containers or conductive containers, or be wrapped in aluminum foil.

- The contents in this document are subject to changes, for improvement and other purposes, without notice. Make sure that this is the latest revision of the document before use.
- Application and operation examples described in this document are quoted for the sole purpose of reference for the use of the products herein and Sanken can assume no responsibility for any infringement of industrial property rights, intellectual property rights or any other rights of Sanken or any third party which may result from its use.
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When considering the use of Sanken products in the applications where higher reliability is required (transportation equipment and its control systems, traffic signal control systems or equipment, fire/crime alarm systems, various safety devices, etc.), and whenever long life expectancy is required even in general purpose electronic equipment or apparatus, please contact your nearest Sanken sales representative to discuss, prior to the use of the products herein.

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• In the case that you use Sanken products or design your products by using Sanken products, the reliability largely depends on the degree of derating to be made to the rated values. Derating may be interpreted as a case that an operation range is set by derating the load from each rated value or surge voltage or noise is considered for derating in order to assure or improve the reliability. In general, derating factors include electric stresses such as electric voltage, electric current, electric power etc., environmental stresses such as ambient temperature, humidity etc. and thermal stress caused due to self-heating of semiconductor products. For these stresses, instantaneous values, maximum values and minimum values must be taken into consideration.

In addition, it should be noted that since power devices or IC's including power devices have large self-heating value, the degree of derating of junction temperature affects the reliability significantly.

- When using the products specified herein by either (i) combining other products or materials therewith or (ii) physically, chemically or otherwise processing or treating the products, please duly consider all possible risks that may result from all such uses in advance and proceed therewith at your own responsibility.
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